Dual P-Channel 20-V (D-S) MOSFET

Key Features:

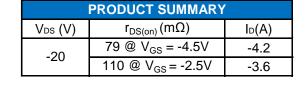
- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

Typical Applications:

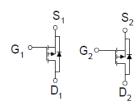
- Battery Powered Instruments
- Portable Computing
- Mobile Phones
- GPS Units and Media Players



ROHS
COMPLIANT
HALOGEN







P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Limit	Units	
Drain-Source Voltage		V _{DS}	-20	V	
Gate-Source Voltage			±8	V	
Continuous Durin Communità	T _A =25°C		-4.2		
Continuous Drain Current ^a	T _A =70°C	l _D	-3.3	Α	
Pulsed Drain Current ^b	I _{DM}	-10			
Continuous Source Current (Diode Conduction) a		Is	-2.3	Α	
Device Discipation 8	T _A =25°C		2.1	W	
Power Dissipation ^a	T _A =70°C	_ rD	1.3		
Operating Junction and Storage Temperature Range			-55 to 150	°C	

THERMAL RESISTANCE RATINGS						
Parameter			Maximum	Units		
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	60	°C/W		
Maximum Junction-to-Ambient	Steady State	IXOJA	110	C/VV		

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

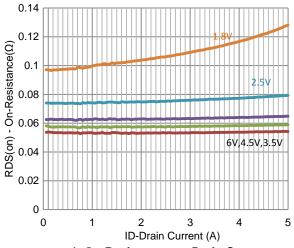
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-0.4			V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			±100	nA
Zero Gate Voltage Drain Current		$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$			1	иA
	I _{DSS}	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10	
On-State Drain Current	I _{D(on)}	$V_{DS} = -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	-10			Α
Drain-Source On-Resistance	r	$V_{GS} = -4.5 \text{ V}, I_D = -3.4 \text{ A}$			79	mΩ
Dialii-Source On-Nesistance	r _{DS(on)}	$V_{GS} = -2.5 \text{ V}, I_D = -2.9 \text{ A}$			110	11122
Forward Transconductance	g _{fs}	$V_{DS} = -15 \text{ V}, I_{D} = -3.4 \text{ A}$		10		S
Diode Forward Voltage	V_{SD}	$I_S = -1.2 \text{ A}, V_{GS} = 0 \text{ V}$		-0.74		V
Dynamic						
Total Gate Charge	Q_g	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V},$		7.6		
Gate-Source Charge	Q_{gs}	$I_{D} = -3.4 \text{ A}$		1.5		nC
Gate-Drain Charge	Q_{gd}	1D = 0.4 A		2.5		
Turn-On Delay Time	t _{d(on)}			7		
Rise Time	t _r	$V_{DD} = -10 \text{ V}, R_L = 2.9 \Omega, I_D = -3.4 \text{ A},$		21		nc
Turn-Off Delay Time	t _{d(off)}	V_{GEN} = -4.5 V, R_{GEN} = 6 Ω		31		ns
Fall Time	t _f			22		
Input Capacitance	C _{iss}			677		
Output Capacitance	C _{oss}	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		92		pF
Reverse Transfer Capacitance	C_{rss}			80		

Notes

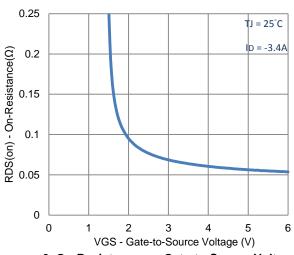
- Pulse test: PW <= 300us duty cycle <= 2%. a.
- Guaranteed by design, not subject to production testing. b.

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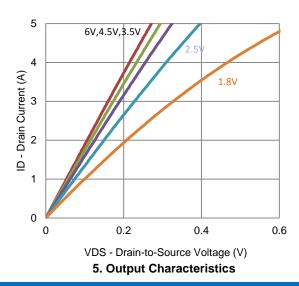
Typical Electrical Characteristics



1. On-Resistance vs. Drain Current



3. On-Resistance vs. Gate-to-Source Voltage

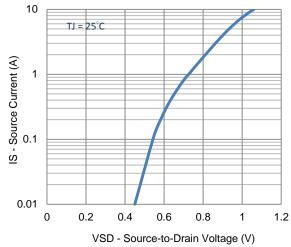


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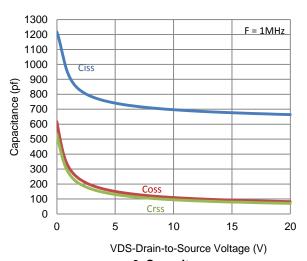
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2. Transfer Characteristics

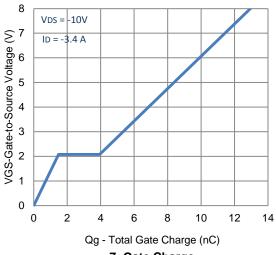


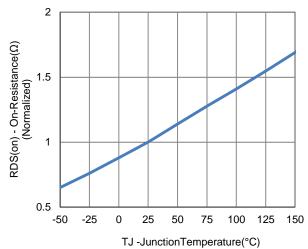
4. Drain-to-Source Forward Voltage



6. Capacitance

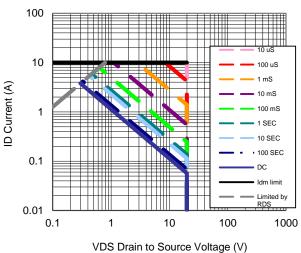
Typical Electrical Characteristics

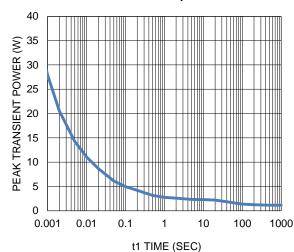




7. Gate Charge

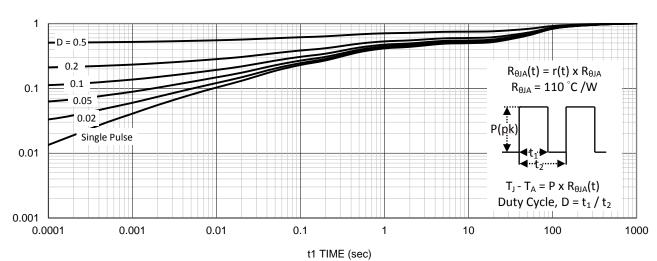
8. Normalized On-Resistance Vs Junction Temperature





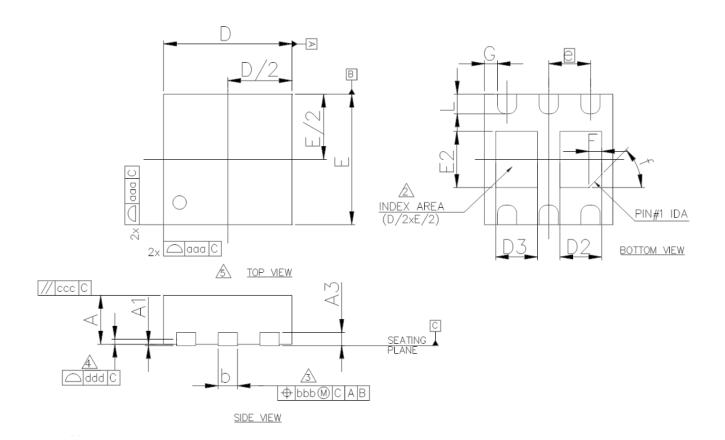
9. Safe Operating Area

10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information



SYMBOL	DIMENSIONS IN MILLIMETERS			
	MIN.	NOM.	MAX.	
A	0.70	0.75	0.80	
A1	0.00	0.02	0.05	
A3		0.20 ref		
Ь	0.25	0.30	0.35	
D		2.00 BSC		
D2	0.60	0.65	0.70	
D3	0.60	0.65	0.70	
E	2.00 BSC			
E2	0.81	0.86	0.91	
e		0.65 BSC		
L	0.25	0.30	0.35	
F	0.20 REF			
f		45?		
G	0.15	0.20	0.25	
aaa	0.15			
bbb	0.10			

DIMENSIONS IN INCHES					
MIN.	NOM.	MAX.			
0.028	0.030	0.032			
0.000	0.001	0.002			
0.010	0.008 ref	0.014			
0.010	0.012 0.079 BSC	0.014			
0.001	910.0				
0.024	0.026	0.028			
0.024	0.026	0.028			
0.079 BSC					
0.032	0.034	0.036			
0.026 BSC					
0.010	0.012	0.014			
0.008 REF					
	45?				
0.006	0.008	0.010			
0.006					
0.004					